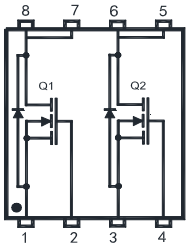
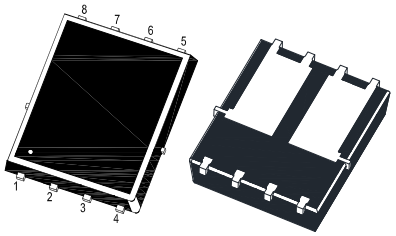
WTM604N060L-AH

Dual N-Channel Enhancement Mode MOSFET

Features

- AEC-Q101 Qualified
- Advanced trench cell design
- Low thermal resistance
- Halogen and Antimony Free(HAF), RoHS compliant





1.Source1 2.Gate1 3.Source2 4.Gate2
5.Drain2 6.Drain2 7.Drain1 8.Drain1
DFN5060 Plastic Package

Applications

- Motor drivers
- DC-DC Converter

Key Parameters

Parameter	Value	Unit
BV_{DSS}	40	V
$R_{DS(ON)}$ Max	9.3 @ V_{GS} = 10 V	mΩ
	10.9 @ V_{GS} = 4.5 V	
$V_{GS(th)}$ typ	1.5	V
Q_g typ	61 @ V_{GS} = 10 V	nC

Absolute Maximum Ratings (at T_a = 25℃ unless otherwise specified) (Q1/Q2)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	T_c = 25℃ T_c = 100℃	I_D	40 25	A
Peak Drain Current, Pulsed [1]		I_{DM}	200	A
Avalanche Current		I_{AS}	34	A
Single Pulse Avalanche Energy [2]		E_{AS}	58	mJ
Power Dissipation	T_c = 25℃	P_D	27	W
Operating Junction and Storage Temperature Range		T_j, T_{stg}	- 55 to + 150	℃

Thermal Characteristics (Q1/Q2)

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	4.5	℃/W
Thermal Resistance from Junction to Ambient [3]	$R_{\theta JA}$	90	℃/W

[1] Pulse Test: Pulse Width ≤ 100 μs, Duty Cycle ≤ 2%, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ = 150°C.

[2] Limited by $T_{J(MAX)}$, starting T_J = 25 °C, L = 0.1 mH, R_g = 25 Ω, I_D = 34 A, V_{GS} = 10 V.

[3] Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Dated: 26/11/2020 Rev: 01

Characteristics at T_a = 25℃ unless otherwise specified (Q1/Q2)

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at I_D = 250 uA	BV_{DSS}	40	-	-	V
Drain-Source Leakage Current at V_{DS} = 32 V	I_{DSS}	-	-	1	μA
Gate Leakage Current at V_{GS} = ± 20 V	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at V_{DS} = V_{GS}, I_D = 250 μA	$V_{GS(th)}$	1	-	2	V
Drain-Source On-State Resistance at V_{GS} = 10 V, I_D = 10 A at V_{GS} = 4.5 V, I_D = 10 A	$R_{DS(on)}$	- -	7.2 -	9.3 10.9	mΩ
DYNAMIC PARAMETERS					
Gate Resistance at V_{DS} = 0 V, f = 1 MHz	R_g	-	1.2	-	Ω
Input Capacitance at V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz	C_{iss}	-	3404	-	pF
Output Capacitance at V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz	C_{oss}	-	232	-	pF
Reverse Transfer Capacitance at V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz	C_{rss}	-	159	-	pF
Gate Charge Total at V_{DS} = 20 V, V_{GS} = 10 V, I_D = 10 A at V_{DS} = 20 V, V_{GS} = 4.5 V, I_D = 10 A	Q_g	- -	61 29	- -	nC
Gate to Source Charge at V_{DS} = 20 V, V_{GS} = 10 V, I_D = 10 A	Q_{gs}	-	12	-	nC
Gate to Drain Charge at V_{DS} = 20 V, V_{GS} = 10 V, I_D = 10 A	Q_{gd}	-	10	-	nC
Turn-On Delay Time at V_{DS} = 20 V, V_{GS} = 10 V, I_D = 10 A, R_g = 4.7 Ω	$t_{d(on)}$	-	26	-	nS
Turn-On Rise Time at V_{DS} = 20 V, V_{GS} = 10 V, I_D = 10 A, R_g = 4.7 Ω	t_r	-	23	-	nS
Turn-Off Delay Time at V_{DS} = 20 V, V_{GS} = 10 V, I_D = 10 A, R_g = 4.7 Ω	$t_{d(off)}$	-	24	-	nS
Turn-Off Fall Time at V_{DS} = 20 V, V_{GS} = 10 V, I_D = 10 A, R_g = 4.7 Ω	t_f	-	4	-	nS
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at I_S = 1 A, V_{GS} = 0 V	V_{SD}	-	-	1.3	V
Body-Diode Continuous Current	I_S	-	-	40	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	200	A
Body Diode Reverse Recovery Time at I_S = 10 A, di/dt = 100 A / μs	t_{rr}	-	13	-	ns
Body Diode Reverse Recovery Charge at I_S = 10 A, di/dt = 100 A / μs	Q_{rr}	-	6	-	nC

Electrical Characteristics Curves (Q1/Q2)

Fig. 1 Typical Output Characteristic

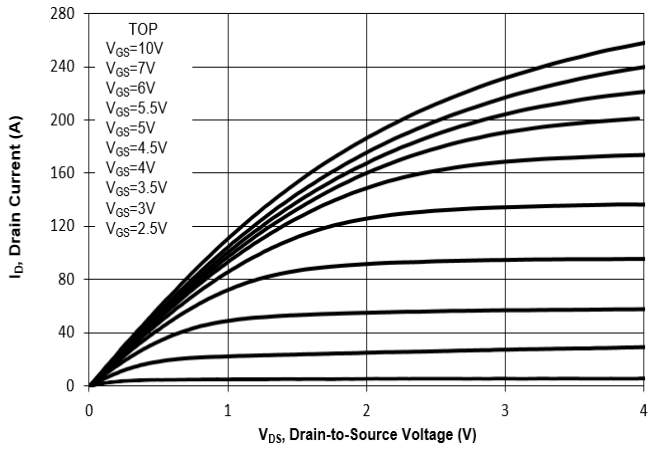


Fig. 2 Typical Transfer Characteristic

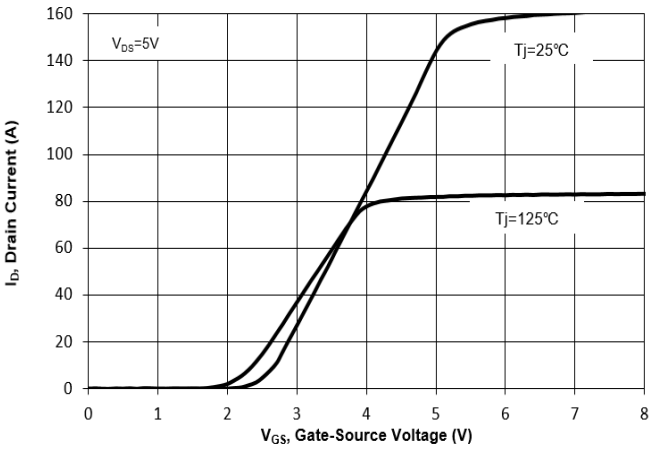


Fig. 3 on-Resistance vs. Drain Current

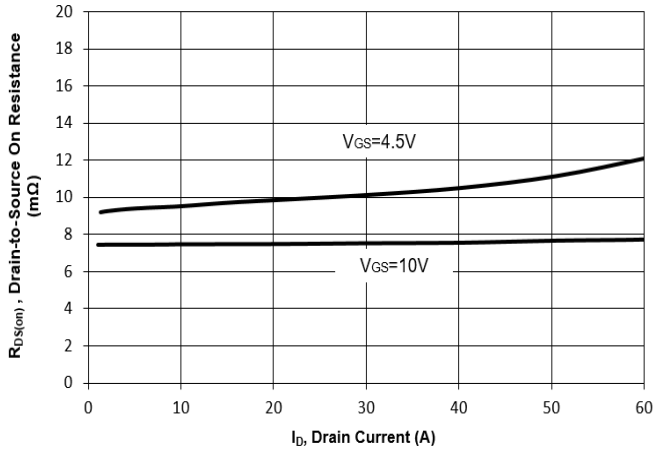


Fig. 4 on-Resistance vs. Gate Voltage

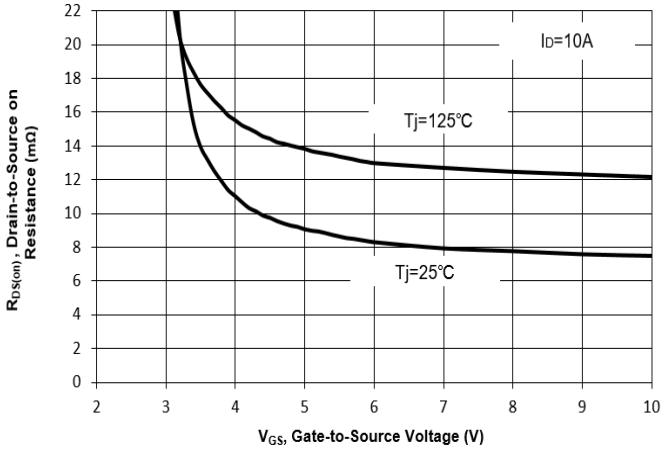


Fig. 5 on-Resistance vs.T_j

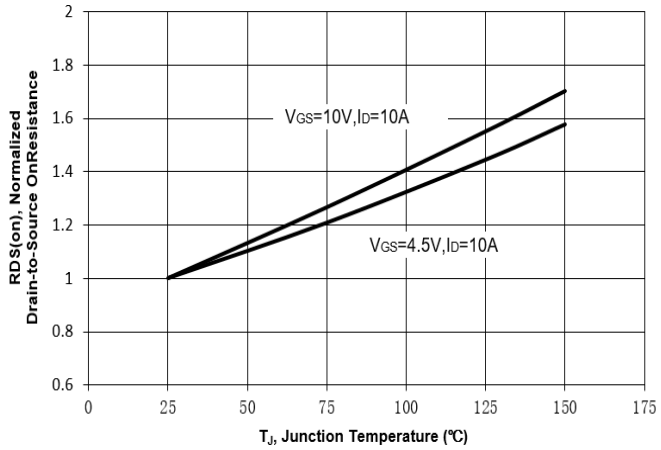
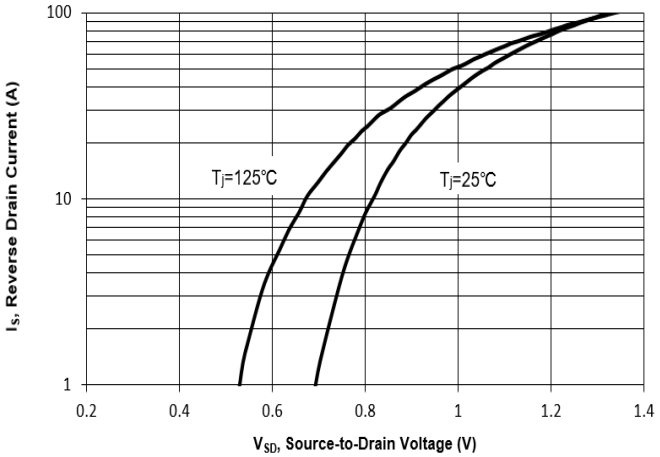


Fig. 6 Typical Body-Diode Forward Characteristic



Electrical Characteristics Curves (Q1/Q2)

Fig. 7 Typical Junction Capacitance

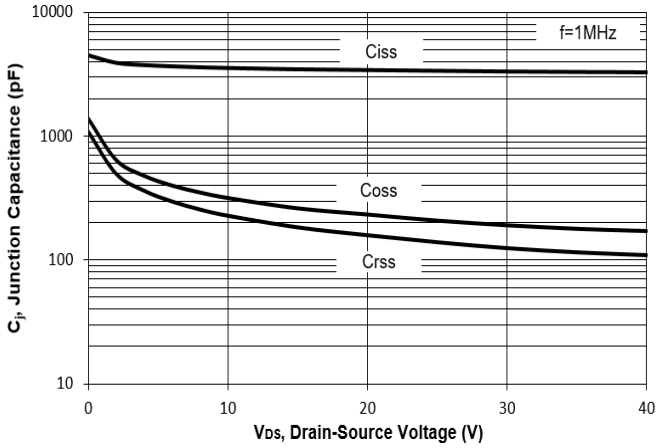


Fig. 8 Drain-Source Leakage Current vs. T_j

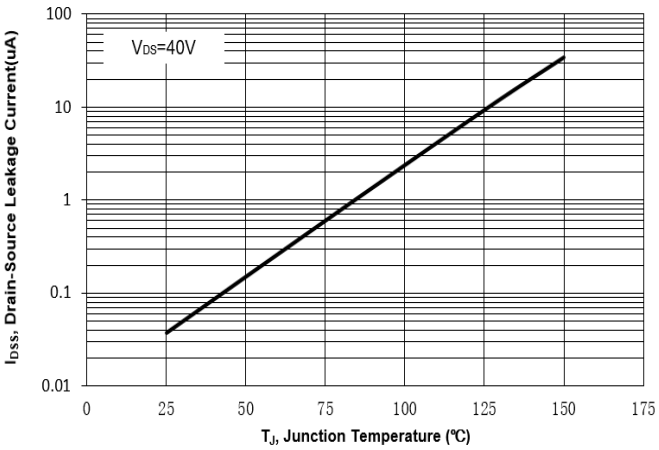


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

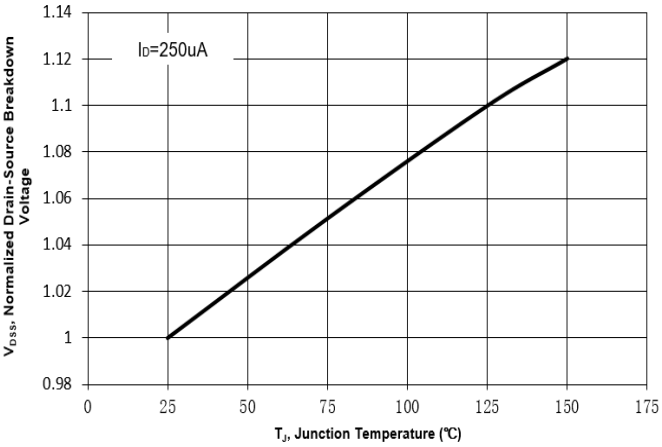


Fig. 10 Gate Threshold Variation vs. T_j

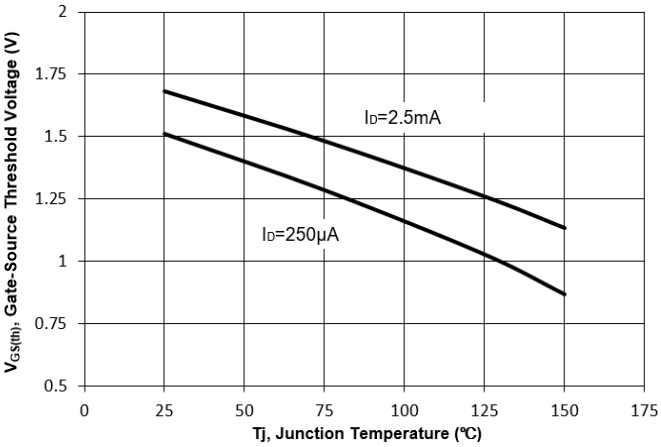


Fig. 11 Gate Charge

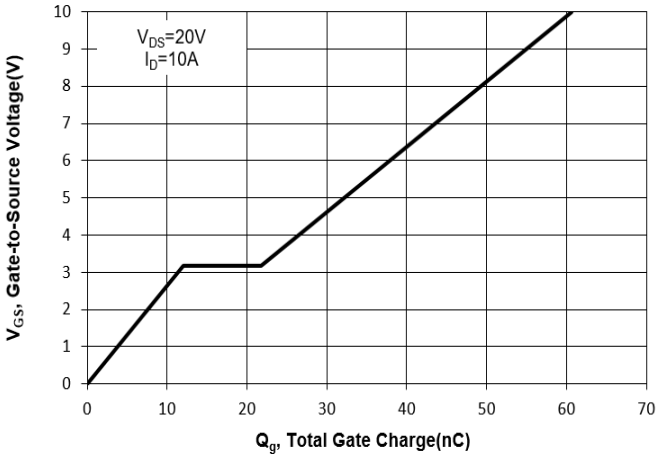
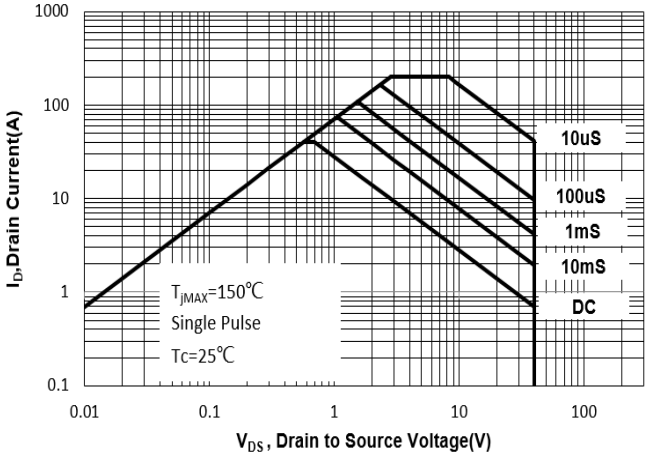


Fig. 12 Safe Operation Area



Electrical Characteristics Curves (Q1/Q2)

Fig.13 Normalized Maximum Transient Thermal Impedance($z_{\Theta JC}$)

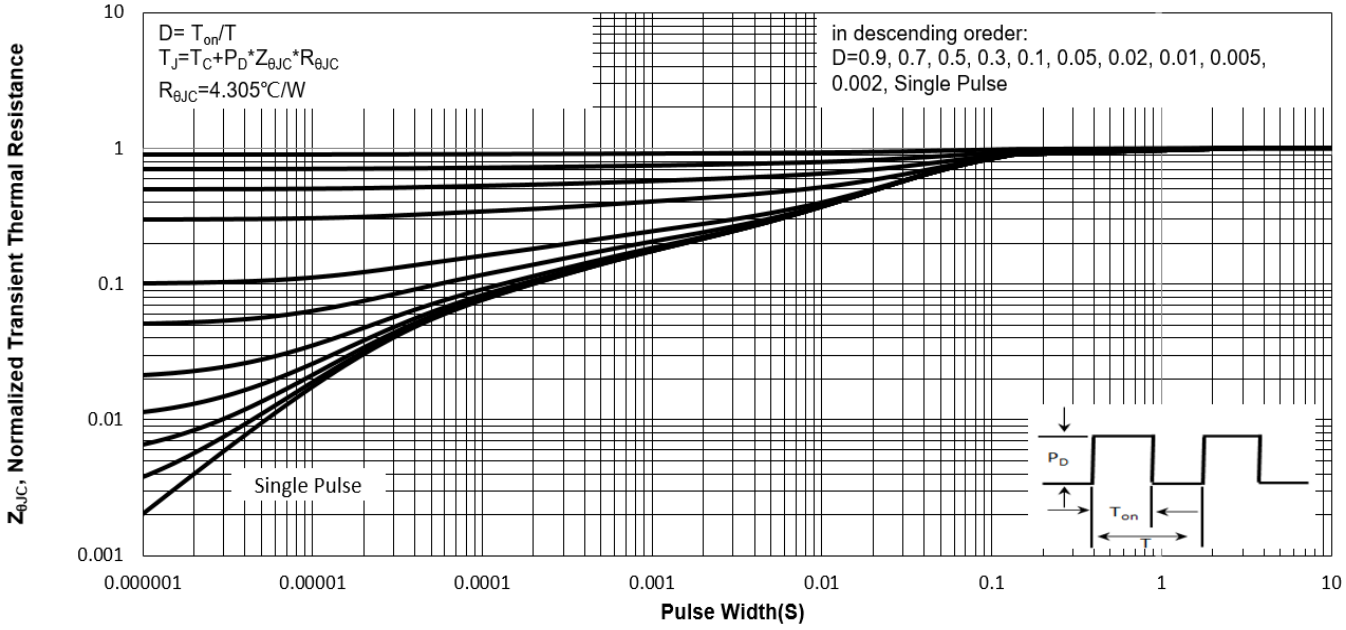
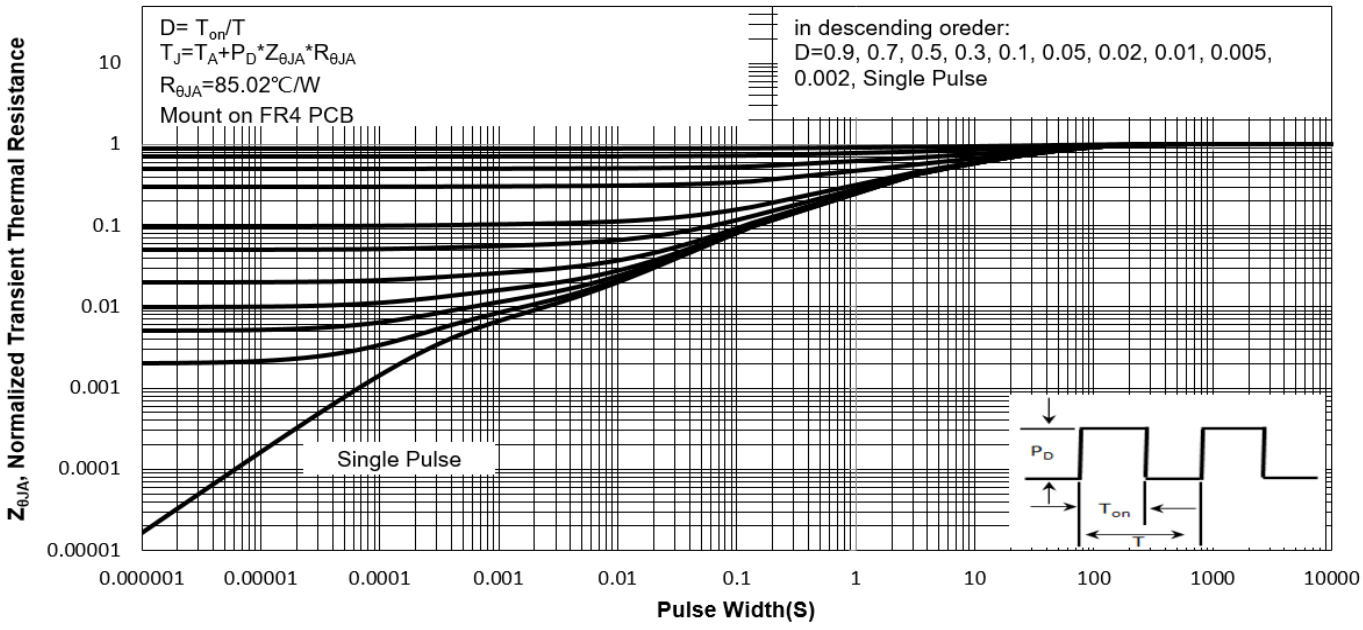


Fig.14 Normalized Maximum Transient Thermal Impedance($z_{\Theta JA}$)



Test Circuits (Q1/Q2)

Fig.1-1 Switching times test circuit

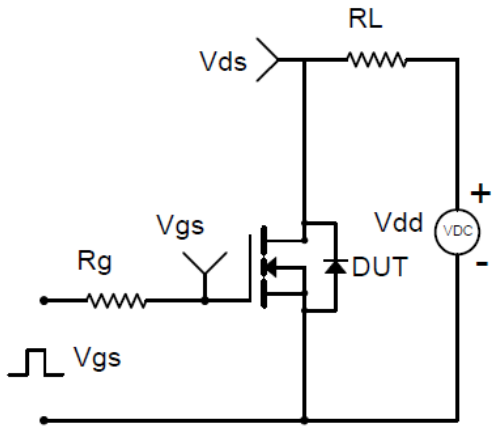


Fig.1-2 Switching Waveform

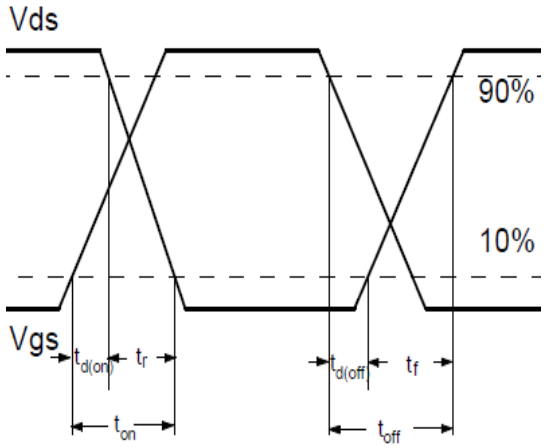


Fig.2-1 Gate charge test circuit

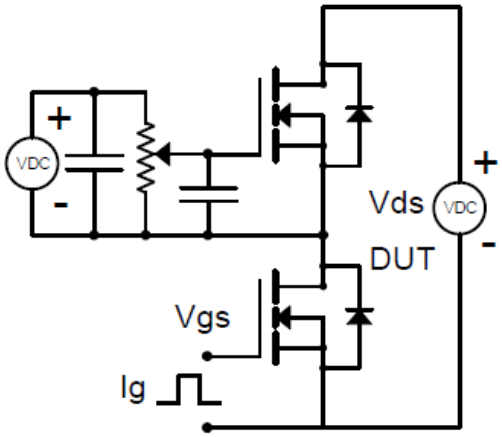


Fig.2-2 Gate charge waveform

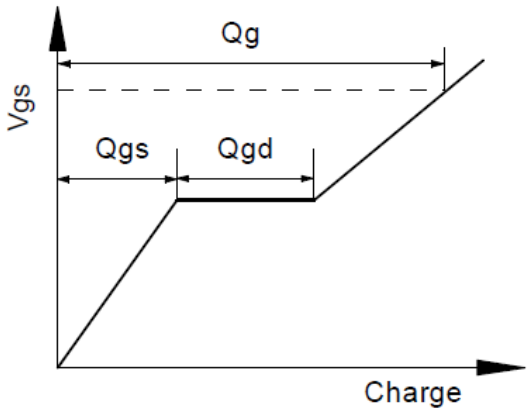


Fig.3-1 Avalanche test circuit

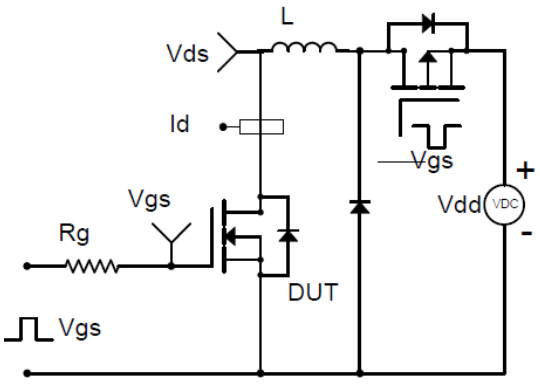
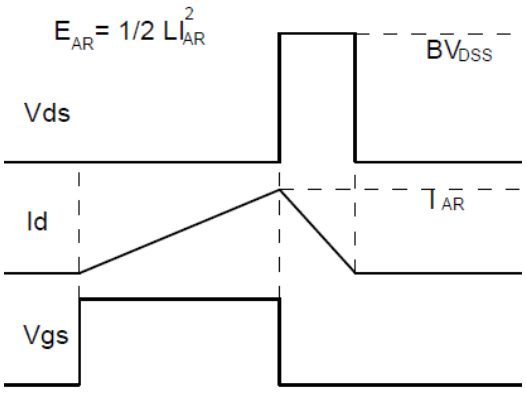
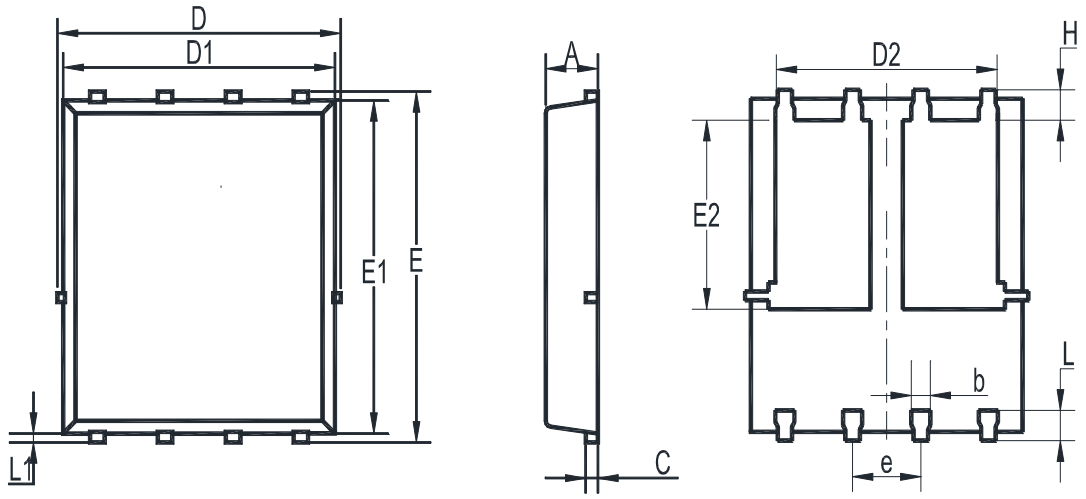


Fig.3-2 Avalanche waveform

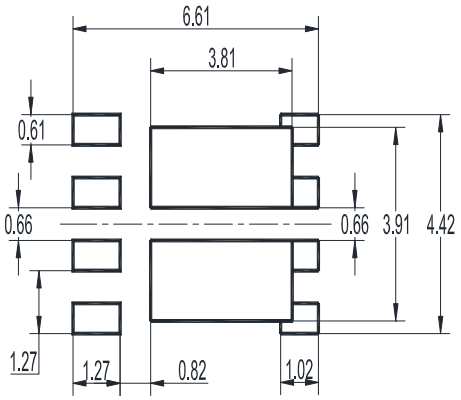


Package Outline Dimensions (Units: mm) DFN5060



UNIT	A	b	C	D	D1	D2	E	E1	E2	e	L	L1	H
mm	1.12 0.9	0.51 0.33	0.34 0.11	5.26 4.7	5.1 4.7	4.5 3.56	6.25 5.75	6 5.6	3.66 3.18	1.37 1.17	0.71 0.35	0.2 0.06	0.71 0.35

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN5060	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Marking information

" TM604N060L " = Part No.

" ****** " = Date Code Marking

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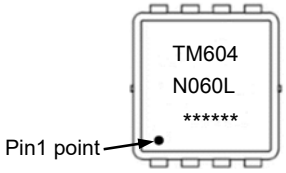

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